FAIRCHILD
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FODM8801A, FODM8801B, FODM8801C OptoHiT™ Series, High Temperature Phototransistor Optocoupler in Half Pitch Mini-Flat 4-Pin Package

Features

- Utilizing patented process technology to achieve high operating temperature up to 125°C
- Guaranteed Current Transfer Ratio (CTR) specifications across full temperature range
  - Excellent CTR linearity at high temperature
  - CTR at very low input current, I_F
- High isolation voltage regulated by safety agency, UL1577, 3750 VAC_{RMS} for 1 min. and DIN EN/IEC60747-5-2 (pending approval)
- Compact half pitch, mini-flat, 4-pin package (1.27mm lead pitch, 2.4mm maximum standoff height)
- > 5mm creepage and clearance distance
- Applicable to Infrared Ray reflow, 245°C

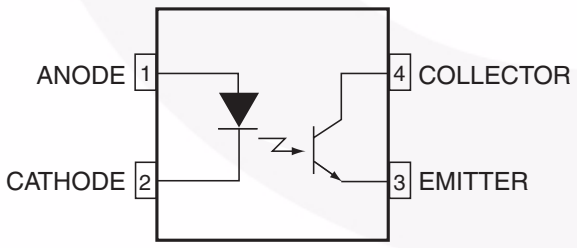
Applications

- Primarily suited for DC-DC converters
- For ground loop isolation, signal to noise isolation
- Communications – adapters, chargers
- Consumer – appliances, set top boxes
- Industrial – power supplies, motor control, programmable logic control

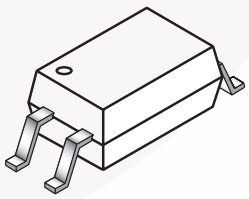
Description

The OptoHiT™ Series, FODM8801, is a first of its kind phototransistor, utilizing Fairchild's leading edge patented process technology to achieving high operating temperature characteristics, up to 125°C. The opto-coupler consists of an aluminum gallium arsenide (AlGaAs) infrared light emitting diode optically coupled to a phototransistor, in a compact half pitch, mini-flat, 4-pin package. It delivers high current transfer ratio at very low input current. The input-output isolation voltage, Viso, is rated at 3750 VAC_{RMS}.

Schematic



Package Drawing



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Safety and Insulation Ratings for Half-Pitch Mini-Flat Package

Symbol	Parameter	Min.	Typ.	Max.	Unit
	Installation Classifications per DIN VDE 0110/1.89 Table 1				
	For rated main voltage < 150Vrms		I-IV		
	For rated main voltage < 300Vrms		I-III		
	Climatic Classification		40/125/21		
	Pollution Degree (DIN VDE 0110/1.89)		2		
CTI	Comparative Tracking Index	175			
V_{PR}	Input to Output Test Voltage, Method b, VIORM x 1.875 = V_{PR},100% Production Test with t_m = 1 sec, Partial Discharge < 5pC	1060			V_{peak}
V_{PR}	Input to Output Test Voltage, Method a, VIORM x 1.5 = V_{PR},Type and Sample Test with t_m = 60 sec, Partial Discharge < 5pC	848			V_{peak}
V_{IORM}	Max Working Insulation Voltage	565			V_{peak}
V_{IOTM}	Highest Allowable Over Voltage	4000			V_{peak}
	External Creepage	5			mm
	External Clearance	5			mm
	Insulation thickness	0.5			mm
	Safety Limit Values- Maximum Values allowed in the event of a failure,				
T_S	Case Temperature	150			°C
$I_{S,INPUT}$	Input Current	200			mA
$P_{S,OUTPUT}$	Output Power	300			mW
R_{IO}	Insulation Resistance at T_S,V_{IO}=500V	10^9			Ω

Absolute Maximum Ratings (T_A = 25°C unless otherwise specified)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Value	Units
TOTAL PACKAGE			
T_{STG}	Storage Temperature	-40 to +150	°C
T_{OPR}	Operating Temperature	-40 to +125	°C
T_J	Junction Temperature	-40 to +140	°C
T_{SOL}	Lead Solder Temperature (Refer to Reflow Temperature Profile on page 11)	260 for 10 sec.	°C
EMITTER			
$I_{F(average)}$	Continuous Forward Current	20	mA
V_R	Reverse Input Voltage	6	V
PD_{LED}	Power Dissipation(1)(3)	40	mW
DETECTOR			
$I_{C(average)}$	Continuous Collector Current	30	mA
V_{CEO}	Collector-Emitter Voltage	75	V
V_{ECO}	Emitter-Collector Voltage	7	V
PD_C	Collector Power Dissipation(2)(3)	150	mW

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Value	Units
T_A	Operating Temperature	-40 to +125	°C
$V_{FL(OFF)}$	Input Low Voltage	-5 to 0.8	V
I_{FH}	Input High Forward Current	1 to 10	mA

Isolation Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{ISO}	Input-Output Isolation Voltage	f = 60Hz, t = 1min., $I_{I-O} \le 10\mu A$(4)(5)	3,750			Vac_{RMS}
R_{ISO}	Isolation Resistance	V_{I-O} = 500V(4)	10^{12}			Ω
C_{ISO}	Isolation Capacitance	Freq. = 1MHz		0.3	0.5	pF

Notes:

1. Derate linearly from 73˚C at a rate of 0.24mW/˚C
2. Derate linearly from 73˚C at a rate of 2.23mW/˚C.
3. Functional operation under these conditions is not implied. Permanent damage may occur if the device is subjected to conditions outside these ratings.
4. Device is considered a two terminal device: Pins 1 and 2 are shorted together and Pins 3 and 4 are shorted together.
5. 3,750 VAC_{RMS} for 1 minute duration is equivalent to 4,500 VAC_{RMS} for 1 second duration.

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Electrical Characteristics

Apply over all recommended conditions (T_A = -40°C to +125°C unless otherwise specified).
All typical values are measured at T_A = 25°C.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
EMITTER						
V_F	Forward Voltage	I_F = 1mA	1.0	1.35	1.8	V
$\Delta V_F / \Delta T_A$	Forward Voltage Coefficient	I_F = 1mA		-1.6		mV / °C
I_R	Reverse Current	V_R = 6V			10	µA
C_T	Terminal Capacitance	V = 0V, f = 1MHz		30		pF
DETECTOR						
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C = 0.5mA, I_F = 0mA	75	130		V
BV_{ECO}	Emitter-Collector Breakdown Voltage	I_E = 100µA, I_F = 0mA	7	12		V
I_{CEO}	Collector Dark Current	V_{CE} = 75V, I_F = 0mA, T_A = 25°C			100	nA
		V_{CE} = 50V, I_F = 0mA			50	µA
		V_{CE} = 5V, I_F = 0mA			30	µA
C_{CE}	Capacitance	V_{CE} = 0V, f = 1MHz		8		pF

Transfer Characteristics

Apply over all recommended conditions (T_A = -40°C to +125°C unless otherwise specified).
All typical values are measured at T_A = 25°C.

Symbol	Parameter	Device	Conditions	Min.	Typ.	Max.	Units
CTR_{CE}	Current Transfer Ratio (collector-emitter)	FODM8801A	I_F = 1.0mA, V_{CE} = 5V @ T_A = 25°C	80	120	160	%
			I_F = 1.0mA, V_{CE} = 5V	35	120	230	%
			I_F = 1.6mA, V_{CE} = 5V	40	125		%
			I_F = 3.0mA, V_{CE} = 5V	45	138		%
		FODM8801B	I_F = 1.0mA, V_{CE} = 5V @ T_A = 25°C	130	195	260	%
			I_F = 1.0mA, V_{CE} = 5V	65	195	360	%
			I_F = 1.6mA, V_{CE} = 5V	70	202		%
			I_F = 3.0mA, V_{CE} = 5V	75	215		%
		FODM8801C	I_F = 1.0mA, V_{CE} = 5V @ T_A = 25°C	200	300	400	%
			I_F = 1.0mA, V_{CE} = 5V	100	300	560	%
			I_F = 1.6mA, V_{CE} = 5V	110	312		%
			I_F = 3.0mA, V_{CE} = 5V	115	330		%
$CTR_{CE(SAT)}$	Saturated Current Transfer Ratio (collector-emitter)	FODM8801A	I_F = 1.0mA, V_{CE} = 0.4V @ T_A = 25°C	65	108	150	%
			I_F = 1.0mA, V_{CE} = 0.4V	30	108		%
			I_F = 1.6mA, V_{CE} = 0.4V	25	104		%
			I_F = 3.0mA, V_{CE} = 0.4V	20	92		%
		FODM8801B	I_F = 1.0mA, V_{CE} = 0.4V @ T_A = 25°C	90	168	245	%
			I_F = 1.0mA, V_{CE} = 0.4V	45	168		%
			I_F = 1.6mA, V_{CE} = 0.4V	40	155		%
			I_F = 3.0mA, V_{CE} = 0.4V	35	132		%
		FODM8801C	I_F = 1.0mA, V_{CE} = 0.4V @ T_A = 25°C	140	238	380	%
			I_F = 1.0mA, V_{CE} = 0.4V	75	238		%
			I_F = 1.6mA, V_{CE} = 0.4V	65	215		%
			I_F = 3.0mA, V_{CE} = 0.4V	55	177		%
$V_{CE(SAT)}$	Saturation Voltage	FODM8801A	I_F = 1.0mA, I_C = 0.3mA		0.17	0.4	V
			I_F = 1.6mA, I_C = 0.4mA		0.16	0.4	V
			I_F = 3.0mA, I_C = 0.6mA		0.15	0.4	V
		FODM8801B	I_F = 1.0mA, I_C = 0.45mA		0.17	0.4	V
			I_F = 1.6mA, I_C = 0.6mA		0.16	0.4	V
			I_F = 3.0mA, I_C = 1.0mA		0.16	0.4	V
		FODM8801C	I_F = 1.0mA, I_C = 0.75mA		0.18	0.4	V
			I_F = 1.6mA, I_C = 1.0mA		0.17	0.4	V
			I_F = 3.0mA, I_C = 1.6mA		0.17	0.4	V

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Switching Characteristics

Apply over all recommended conditions (T_A = -40°C to +125°C unless otherwise specified).
All typical values are measured at T_A = 25°C.

Symbol	Parameter	Device	Conditions	Min.	Typ.	Max.	Units
t_{ON}	Turn On Time	All Devices	I_F = 1.6mA, V_{CC} = 5V, R_L = 0.75kΩ	1	6	20	µs
			I_F = 1.6mA, V_{CC} = 5V, R_L = 4.7kΩ		6		µs
t_{OFF}	Turn Off Time	All Devices	I_F = 1.6mA, V_{CC} = 5V, R_L = 0.75kΩ	1	6	20	µs
			I_F = 1.6mA, V_{CC} = 5V, R_L = 4.7kΩ		40		µs
t_R	Output Rise Time (10% to 90%)	All Devices	I_F = 1.6mA, V_{CC} = 5V, R_L = 0.75kΩ		5		µs
t_F	Output Fall Time (90% to 10%)	All Devices	I_F = 1.6mA, V_{CC} = 5V, R_L = 0.75kΩ		5.5		µs
CM_H	Common Mode Rejection Voltage (Transient Immunity) – Output High	All Devices	T_A = 25°C, I_F = 0mA, V_O > 2.0V, R_L = 4.7kΩ, V_{CM} = 1000V[6], Figure 14		20		kV / µs
CM_L	Common Mode Rejection Voltage (Transient Immunity) – Output Low	All Devices	T_A = 25°C, I_F = 1.6mA, V_O < 0.8V, R_L = 4.7kΩ, V_{CM} = 1000V[6], Figure 14		20		kV / µs

Note:

6. Common mode transient immunity at output high is the maximum tolerable positive dVcm/dt on the leading edge of the common mode impulse signal, Vcm, to assure that the output will remain high.

Typical Performance Curves

Fig. 1 Forward Current vs. Forward Voltage

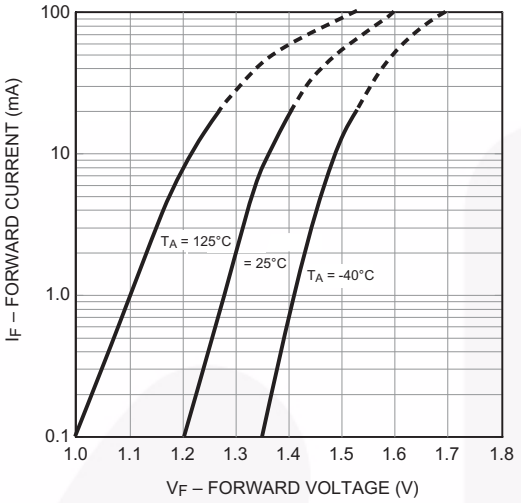


Fig. 2 Collector Current vs. Forward Current

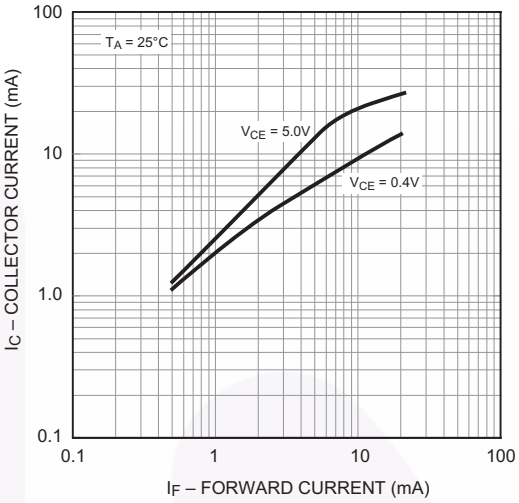


Fig. 3 Current Transfer Ratio vs. Forward Current

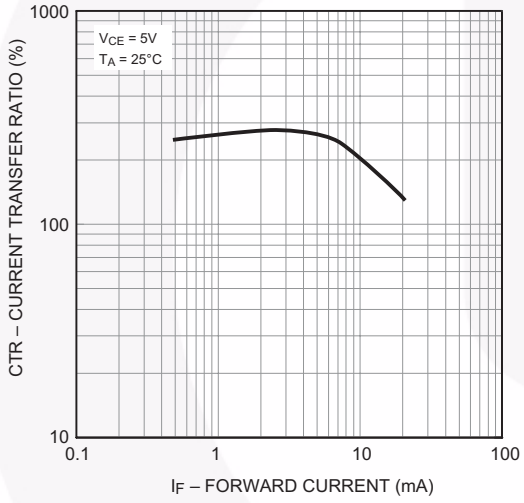


Fig. 4 Normalized CTR vs. Forward Current

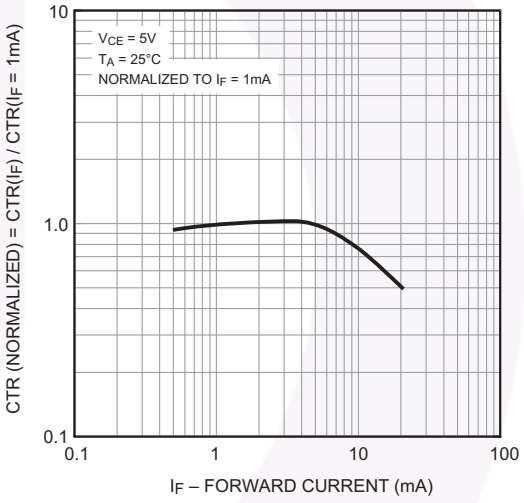


Fig. 5 Normalized CTR vs. Ambient Temperature

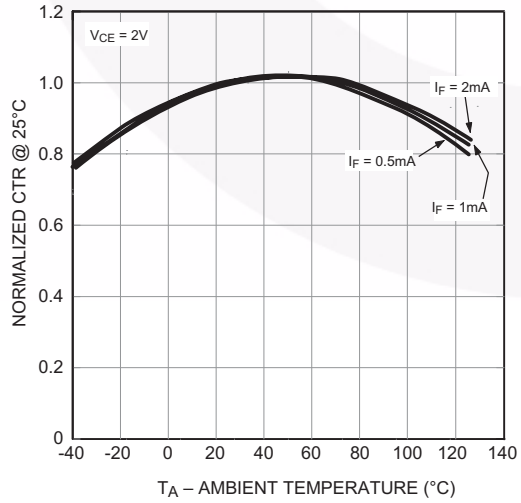
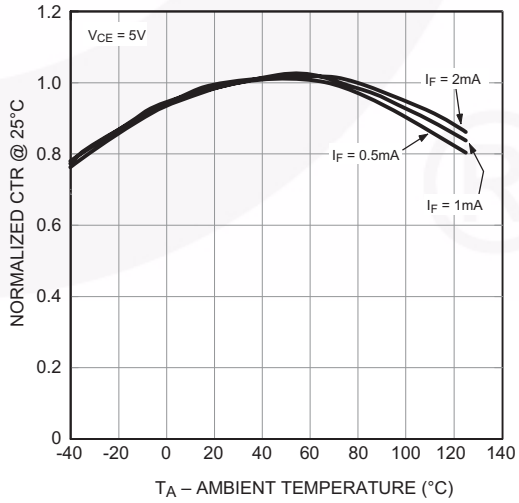


Fig. 6 Normalized CTR vs. Ambient Temperature



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Typical Performance Curves (Continued)

Fig. 7 Collector Current vs. Ambient Temperature

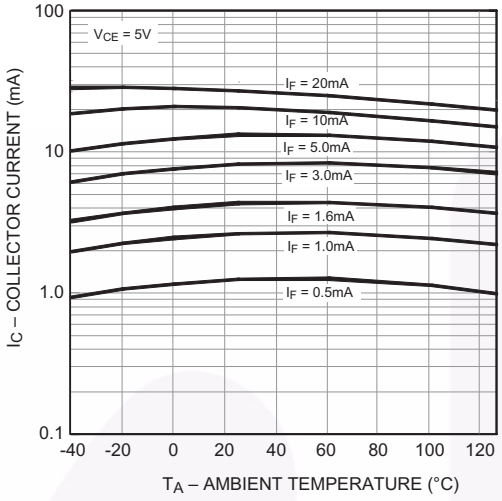


Fig. 8 Collector Current vs. Collector-Emitter Voltage

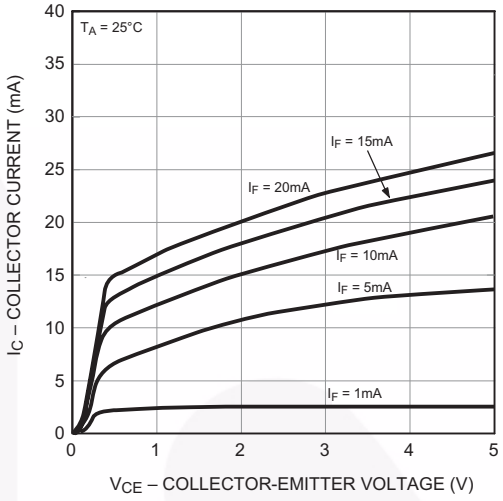


Fig. 9 Collector Dark Current vs. Ambient Temperature

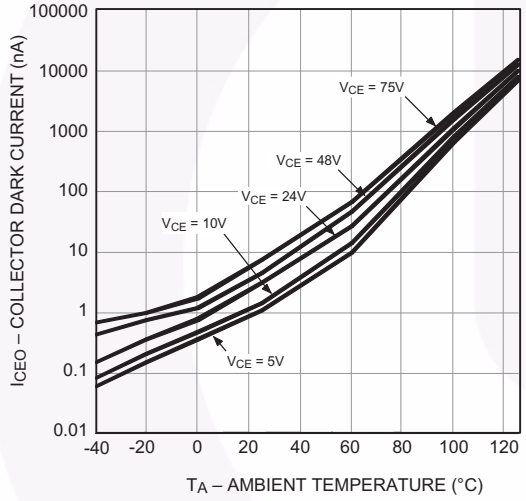


Fig. 10 Switching Time vs. Load Resistance

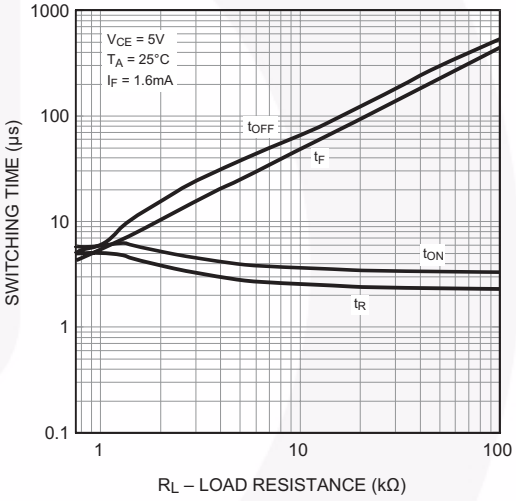


Fig. 11 Collector-Emitter Saturation Voltage vs. Ambient Temperature

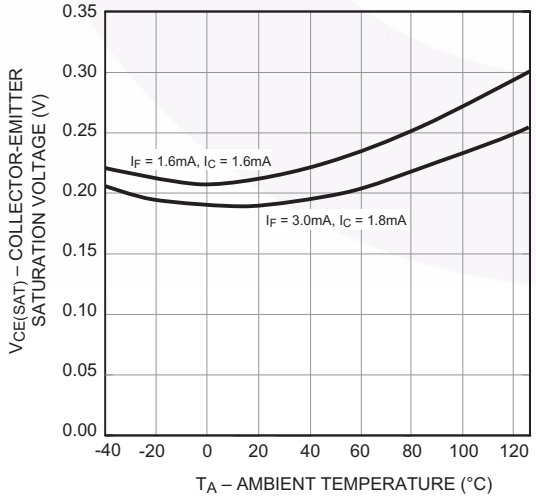
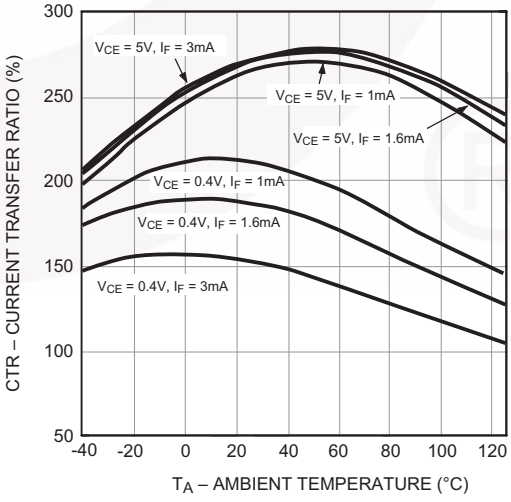


Fig. 12. Current Transfer Ration vs. Ambient Temperature



Test Circuits

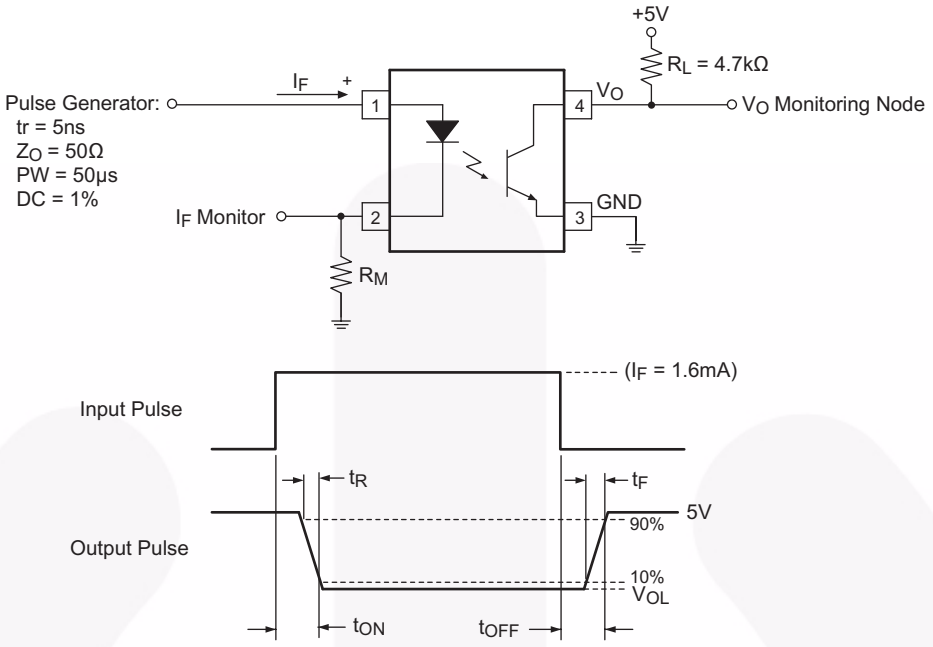


Figure 13. Test Circuit for Propagation Delay Time, Rise Time and Fall Time

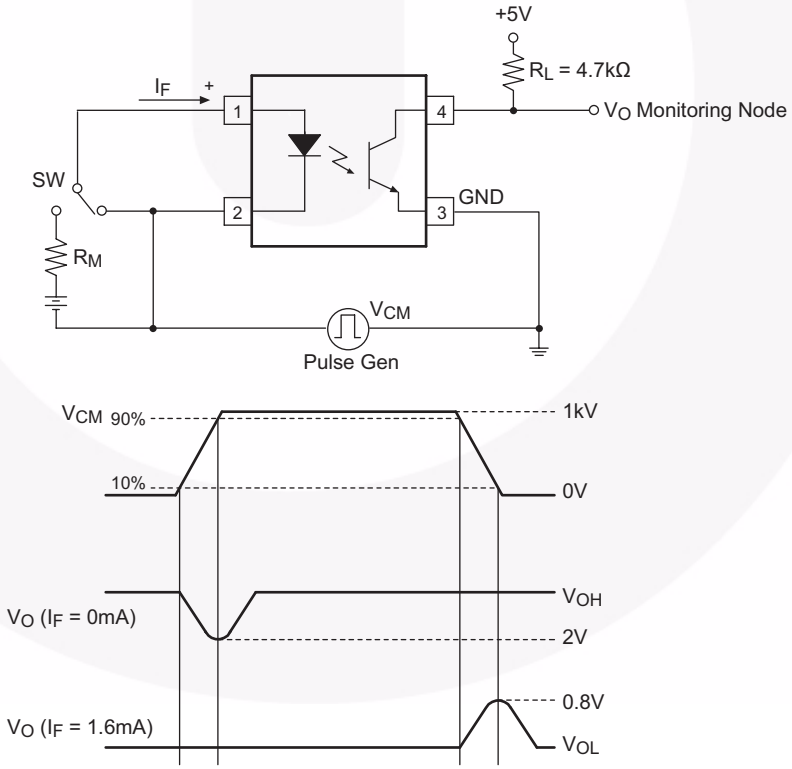
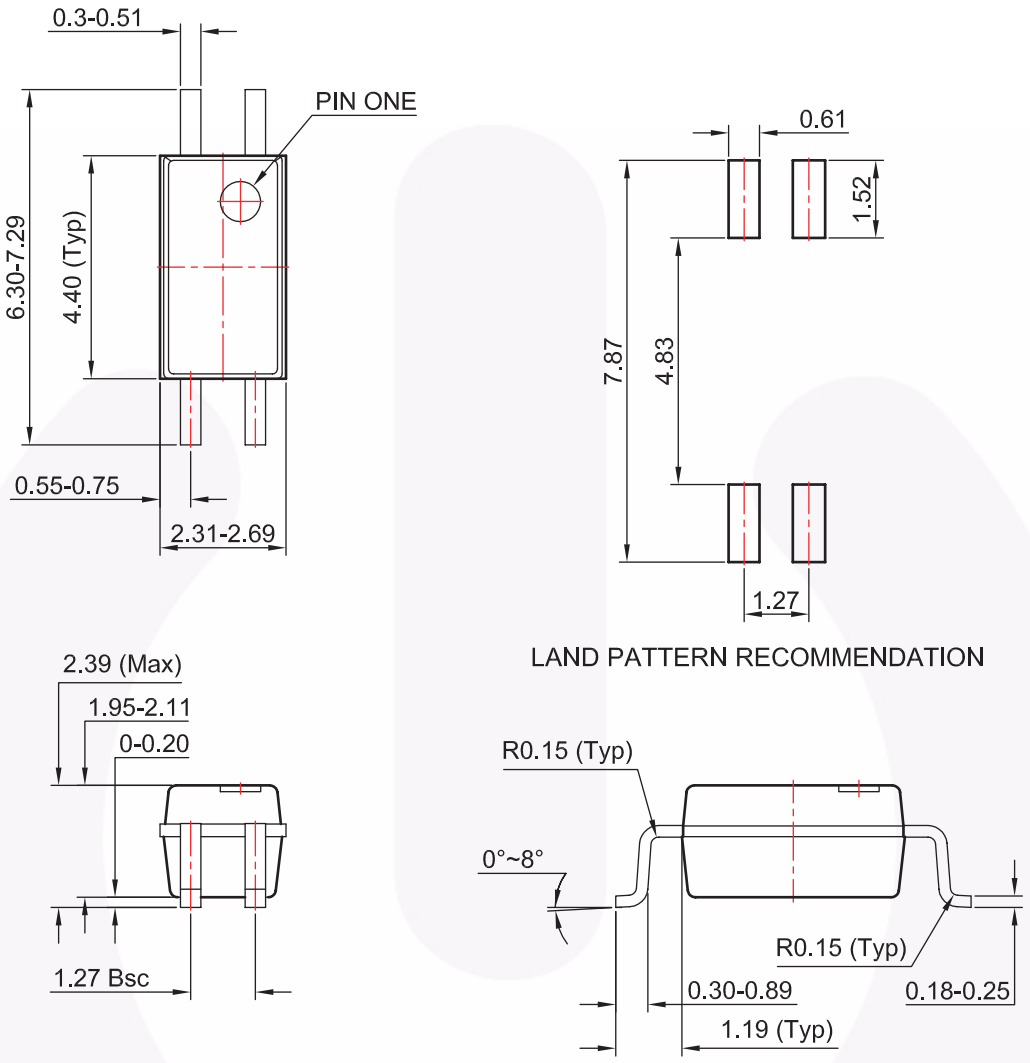


Figure 14. Test Circuit for Instantaneous Common Mode Rejection Voltage

Package Dimensions



Note:
All dimensions are in millimeters.

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:
http://www.fairchildsemi.com/packaging/

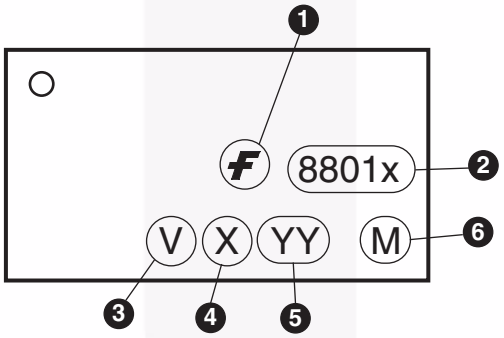
Ordering Information

Part Number	Current Transfer Ratio (CTR %) Option, I_F = 1mA, V_{CE} = 5V
FODM8801A	80% to 160%
FODM8801B	130% to 260%
FODM8801C	200% to 400%
Packing Method	
FODM8801*x*	Tube (100 units per tube)
FODM8801*xR2*	Tape and Reel (2500 units per reel)
FODM8801*xV*	Tube (100 units per tube), DIN/EN IEC60747-5-2 (pending approval)
FODM8801*xR2V*	Tape and Reel (2500 units per reel), DIN/EN IEC60747-5-2 (pending approval)

All packages are lead free per JEDEC: J-STD-020B standard.

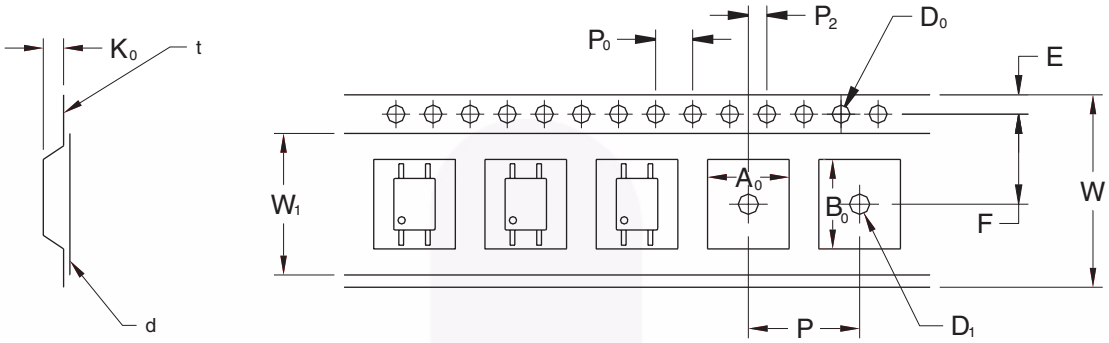
"x" or "xR2" denotes the Current Transfer Ratio option. For example FODM8801AR2 is a phototransistor with 80% to 160% CTR in tape and reel packaging.

Marking Information



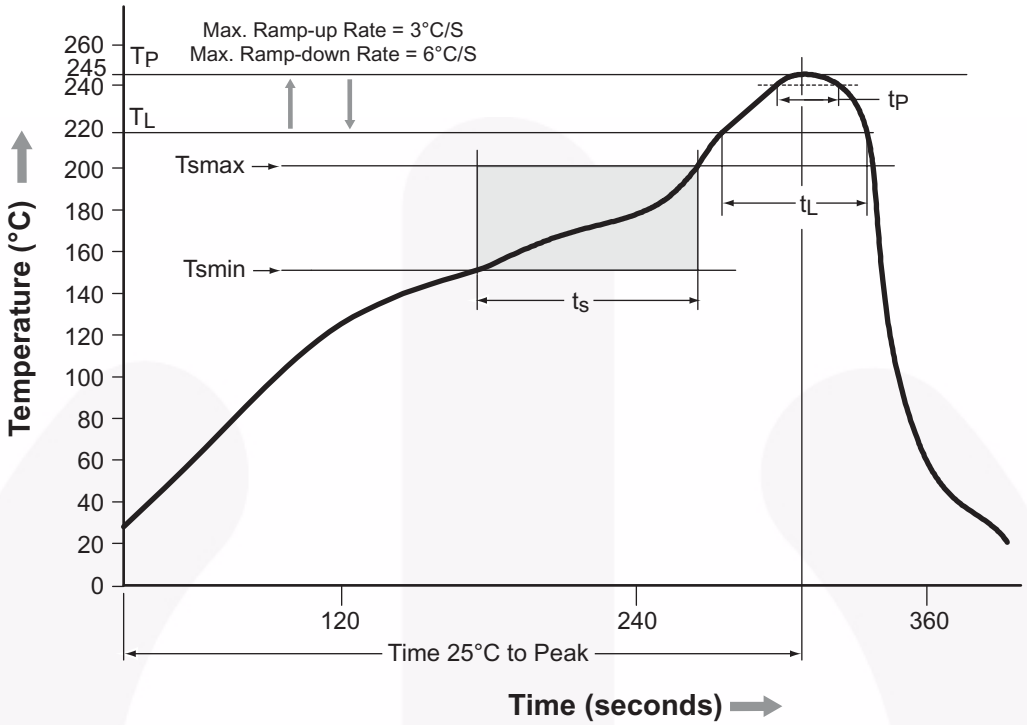
Definitions	
1	Fairchild logo
2	Device number, 'x' denotes CTR% option (A, B or C)
3	VDE mark (Note: Only appears on parts ordered with DIN/EN IEC60747-5-2 option – See order entry table)
4	One digit year code, e.g., '1' represents the year 2011
5	Two digit work week ranging from '01' to '53'
6	Assembly package code

Tape and Reel Dimensions



		1.27 Pitch
Description	**Symbol**	**Dimensions (mm)**
Tape Width	W	12.00 +0.30/-0.10
Tape Thickness	t	0.30 ±0.05
Sprocket Hole Pitch	P_0	4.00 ±0.10
Sprocket Hole Diameter	D_0	1.50 +0.10/-0.0
Sprocket Hole Location	E	1.75 ±0.10
Pocket Location	F	5.50 ±0.10
	P_2	2.00 ±0.10
Pocket Pitch	P	8.00 ±0.10
Pocket Dimension	A_0	2.80 ±0.10
	B_0	7.30 ±0.10
	K_0	2.30 ±0.10
Pocket Hole Diameter	D_1	1.50 Min.
Cover Tape Width	W_1	9.20
Cover Tape Thickness	d	0.065 ±0.010
Max. Component Rotation or Tilt		10° Max.
Devices Per Reel		2500
Reel Diameter		330mm (13")

Reflow Profile



Profile Freature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (t_S) from (Tsmin to Tsmax)	60–120 seconds
Ramp-up Rate (t_L to t_P)	3°C/second max.
Liquidous Temperature (T_L)	217°C
Time (t_L) Maintained Above (T_L)	60–150 seconds
Peak Body Package Temperature	245°C +0°C / –5°C
Time (t_P) within 5°C of 260°C	30 seconds
Ramp-down Rate (T_P to T_L)	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

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CorePOWER™
CROSSVOLT™
CTL™
Current Transfer Logic™
DEUXPEED®
Dual Cool™
EcoSPARK®
EfficientMax™
ESBC™
F®
Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FAST®
FastvCore™
FETBench™
FlashWriter®*
FPS™
F-PFS™
FRFET®
Global Power Resource℠
Green FPS™
Green FPS™ e-Series™
Gmax™
GTO™
IntelliMAX™
ISOPLANAR™
MegaBuck™
MICROCOUPLER™
MicroFET™
MicroPak™
MicroPak2™
MillerDrive™
MotionMax™
Motion-SPM™
mWSaver™
OptoHiT™
OPTOLOGIC®
OPTOPLANAR®
®
PDP SPM™
Power-SPM™
PowerTrench®
PowerXS™
Programmable Active Droop™
QFET®
QS™
Quiet Series™
RapidConfigure™
™
Saving our world, 1mW/W/kW at a time™
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SmartMax™
SMART START™
SPM®
STEALTH™
SuperFET®
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SupreMOS®
SyncFET™
Sync-Lock™
SYSTEM GENERAL®*
The Power Franchise®
The Right Technology for Your Success™
the power franchise
TinyBoost™
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TINYOPTO™
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Definition of Terms

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